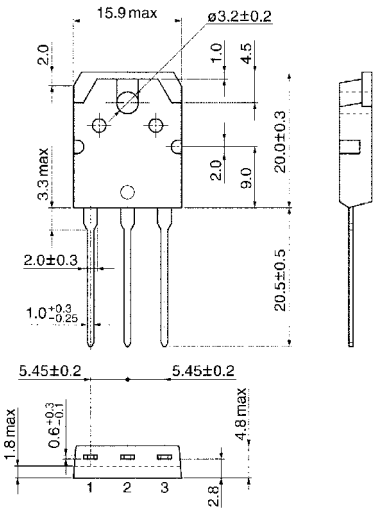
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

2SK1529

High Power Amplifier Application

- High breakdown voltage : V_{DSS} = 180V
- High forward transfer admittance : $|Y_{fs}|$ = 4.0 S (typ.)
- Complementary to 2SJ200

Unit: mm



1. GATE
2. DRAIN (HEAT SINK)
3. SOURCE

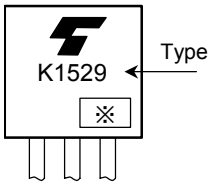
JEDEC	—
JEITA	—
TOSHIBA	2-16C1B

Weight: 4.6 g (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Drain−source voltage	V_{DSS}	180	V
Gate−source voltage	V_{GSS}	±20	V
Drain current (Note 1)	I_D	10	A
Drain power dissipation (Tc = 25°C)	P_D	120	W
Channel temperature	T_c	150	°C
Storage temperature range	T_{stg}	−55~150	°C

Marking



Type ※ Lot Number

Month (starting from alphabet A)

Year (last number of the christian era)

Electrical Characteristics (Ta = 25°C)

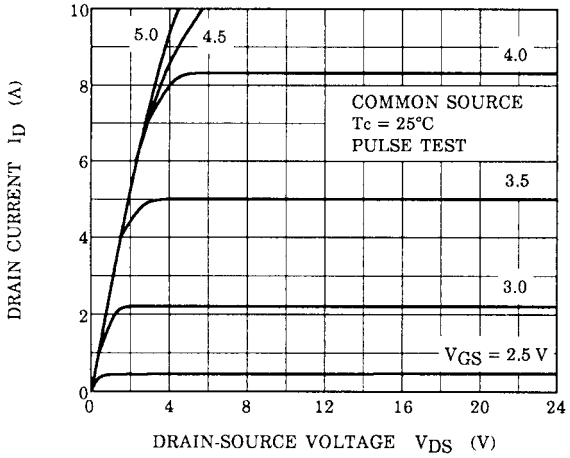
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Drain cut−off current	I_{DSS}	V_{DS} = 180 V, V_{GS} = 0	—	—	1.0	mA
Gate leakage current	I_{GSS}	V_{DS} = 0, V_{GS} = ±20 V	—	—	±0.5	μA
Drain−source breakdown voltage	$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0	180	—	—	V
Drain−source saturation voltage	$V_{DS\ (ON)}$	I_D = 6 A, V_{GS} = 10 V	—	2.5	5.0	V
Gate−source cut−off voltage (Note 2)	$V_{GS\ (OFF)}$	V_{DS} = 10 V, I_D = 0.1 A	0.8	—	2.8	V
Forward transfer admittance	$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 3 A	—	4.0	—	S
Input capacitance	C_{iss}	V_{DS} = 30 V, V_{GS} = 0, f = 1 MHz	—	700	—	pF
Output capacitance	C_{oss}	V_{DS} = 30 V, V_{GS} = 0, f = 1 MHz	—	150	—	
Reverse transfer capacitance	C_{rss}	V_{DD} ≈ 30 V, V_{GS} = 0, f = 1 MHz	—	90	—	

Note 1: Please use devices on condition that the channel temperature is below 150°C.

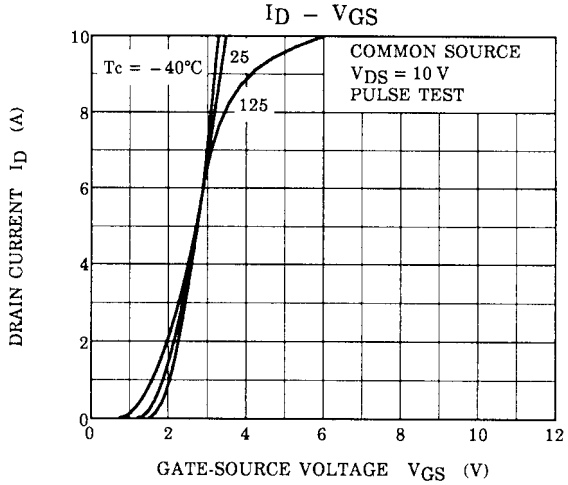
Note 2: $V_{GS\ (OFF)}$ Classification 0: 0.8~1.6 Y: 1.4~2.8

This transistor is an electrostatic sensitive device.
Please handle with caution.

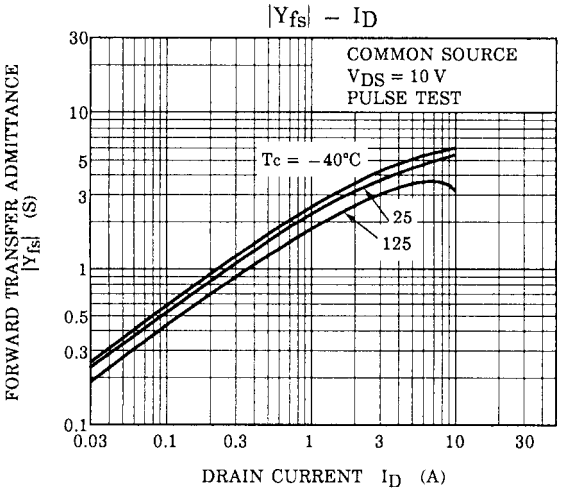
I_D – V_{DS}



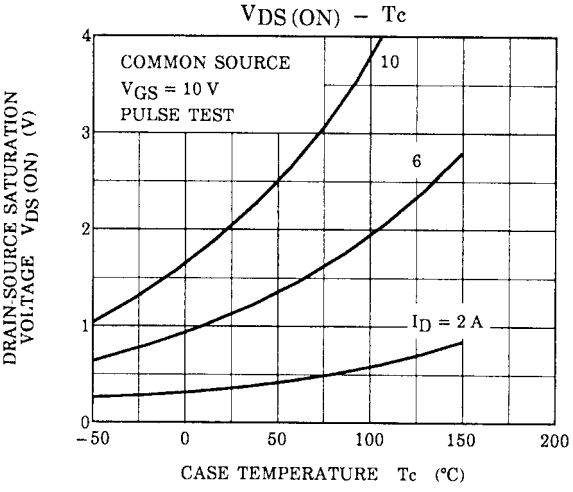
I_D – V_{GS}



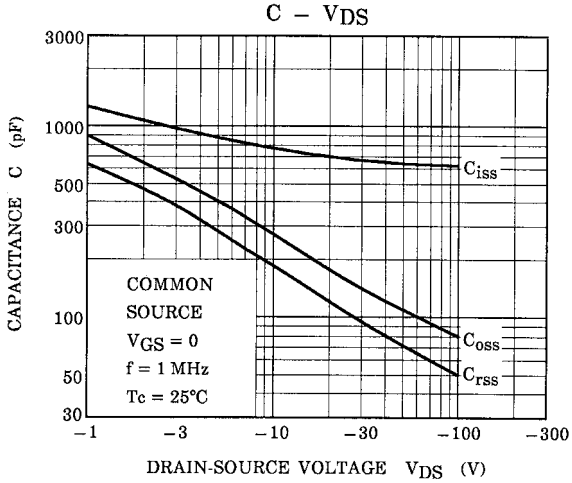
$|Y_{fs}|$ – I_D



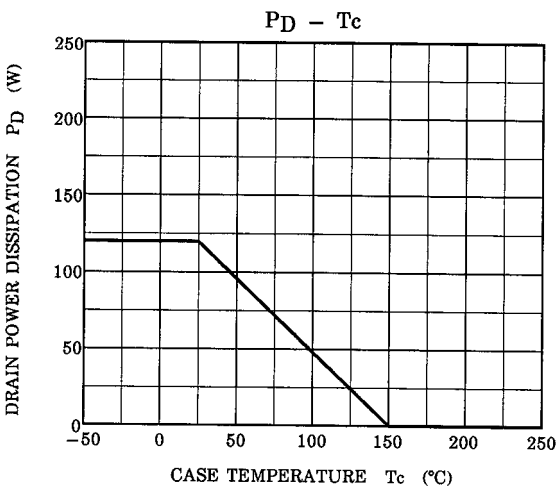
$V_{DS\,(ON)}$ – Tc

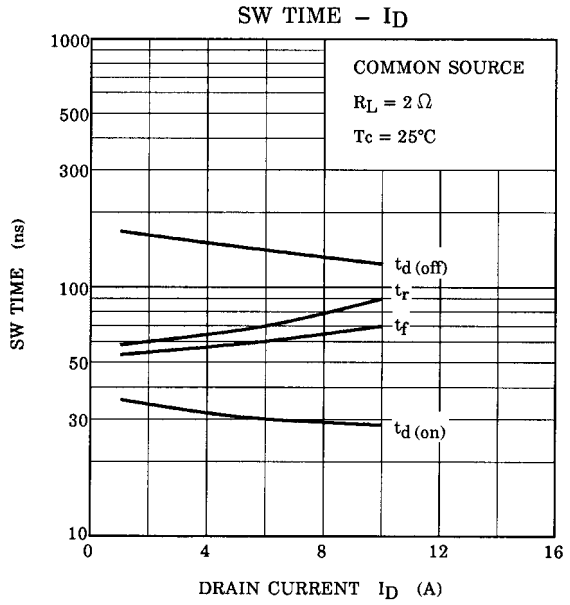


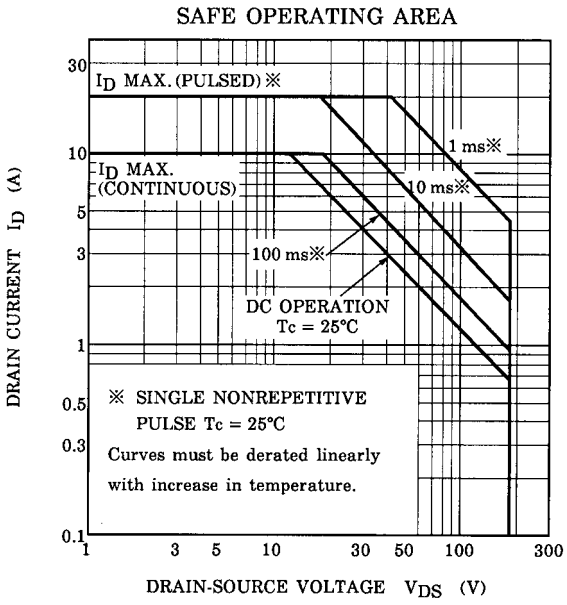
C – V_{DS}



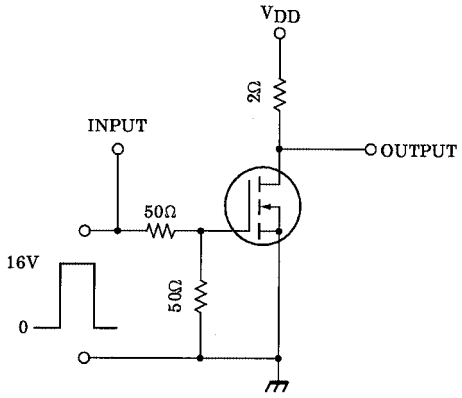
P_D – Tc







Switching Time Test Circuit



Waveforms